

# C2D05120A-Silicon Carbide Schottky Diode

# ZERO RECOVERY® RECTIFIER

 $\mathbf{V}_{\mathsf{RRM}} = 1200 \ \mathsf{V}$ 

 $I_{c} = 5 A$ 

 $\mathbf{Q_c} = 28 \text{ nC}$ 

Marking

C2D05120

## **Features**

- 1200-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V<sub>F</sub>

## **Benefits**

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

# PIN 1O PIN 2O-

**Package** 

TO-220-2

**Part Number** 

C2D05120A

# O CASE

**Package** 

TO-220-2

## **Applications**

- Switch Mode Power Supplies
- Power Factor Correction
- **Motor Drives**
- High Voltage Multipliers

Maximum Ratings					
Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{_{\mathrm{RRM}}}$	Repetitive Peak Reverse Voltage	1200	V		
$V_{RSM}$	Surge Peak Reverse Voltage	1200	V		
V <sub>DC</sub>	DC Blocking Voltage	1200	V		
$I_{\text{F(AVG)}}$	Average Forward Current	5 10	А	T <sub>c</sub> =160°C, DC T <sub>c</sub> =125°C, DC	
$\boldsymbol{I}_{\text{F(PEAK)}}$	Peak Forward Current	15	А	T <sub>C</sub> =125°C, T <sub>REP</sub> <1mS, Duty=0.5	
$\boldsymbol{I}_{\text{FRM}}$	Repetitive Peak Forward Surge Current	30	А	$T_{c}$ =25°C, $t_{p}$ =10 ms, Half Sine Wave	
$\mathbf{I}_{FSM}$	Non-Repetitive Peak Forward Surge Current	100	А	T <sub>C</sub> =25°C, t <sub>P</sub> =10 μs, Pulse	
$P_{tot}$	Power Dissipation	136 45	W	T <sub>c</sub> =25°C T <sub>c</sub> =125°C	
$T_{_\mathtt{J}}$ , $T_{_{\mathtt{stg}}}$	Operating Junction and Storage Temperature	-55 to +175	°C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	



## **Electrical Characteristics**

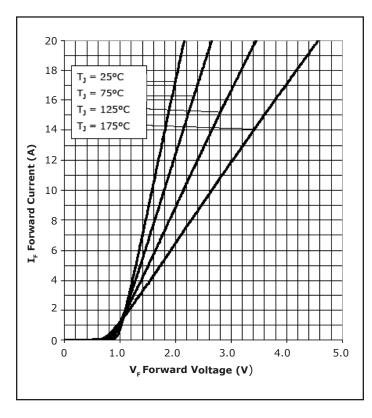
Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.6 2.6	1.8 3.0	V	$I_F = 5 \text{ A } T_J = 25^{\circ}\text{C}$ $I_F = 5 \text{ A } T_J = 175^{\circ}\text{C}$	
$I_R$	Reverse Current	50 100	200 1000	μΑ	$V_R = 1200 \text{ V } T_J = 25^{\circ}\text{C}$ $V_R = 1200 \text{ V } T_J = 175^{\circ}\text{C}$	
Q <sub>c</sub>	Total Capacitive Charge	28		nC	$V_R = 1200 \text{ V, } I_F = 5 \text{ A}$ $di/dt = 500 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	
С	Total Capacitance	455 45 33		pF	$V_R = 0 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 200 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$ $V_R = 400 \text{ V, } T_J = 25^{\circ}\text{C, } f = 1 \text{ MHz}$	

### Note:

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Unit
$R_{_{ heta JC}}$	Thermal Resistance from Junction to Case	1.1	°C/W

## **Typical Performance**





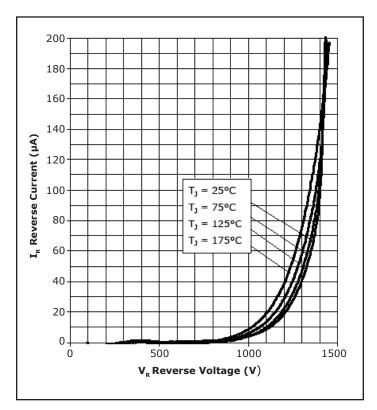
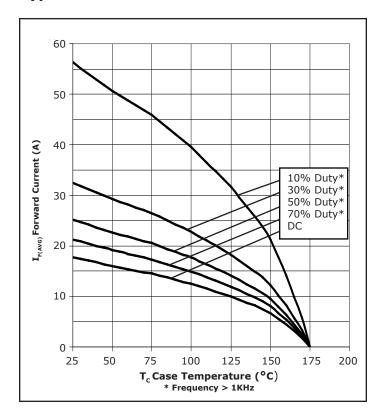


Figure 2. Reverse Characteristics

<sup>1.</sup> This is a majority carrier diode, so there is no reverse recovery charge.



## **Typical Performance**



400
350
300
250
200
150
100
50
0
100
V<sub>R</sub> Reverse Voltage (V)

Figure 3. Current Derating

Figure 4. Capacitance vs. Reverse Voltage

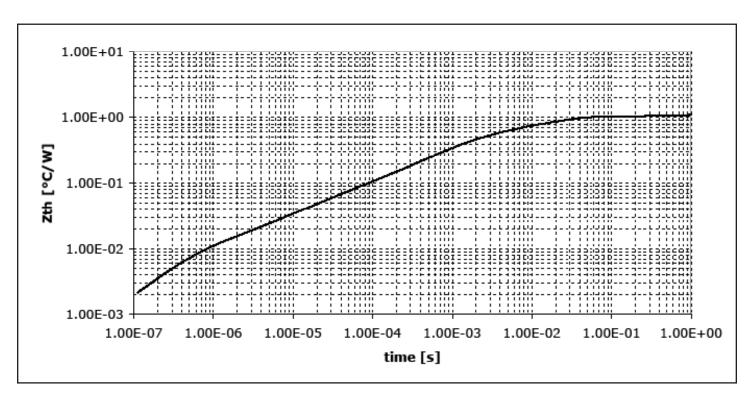


Figure 5. Transient Thermal Impedance

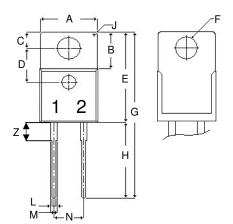


## **Package Dimensions**

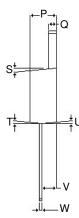
Package TO-220-2

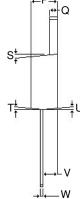
PIN 1O

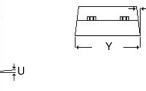
PIN 2O-



O CASE







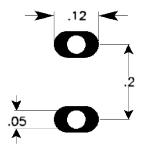
noc.	Inc	hes	Millimeters		
POS	Min	Max	Min	Max	
А	.381	.410	9.677	10.414	
В	.235	.255	5.969	6.477	
С	.100	.120	2.540	3.048	
D	.223	.337	5.664	8.560	
E	.590	.615	14.986	15.621	
F	.143	.153	3.632	3.886	
G	1.105	1.147	28.067	29.134	
Н	.500	.550	12.700	13.970	
J	R 0.197		R 0.197		
L	.025	.036	.635	.914	
М	.045	.055	1.143	1.397	
N	.195	.205	4.953	5.207	
Р	.165	.185	4.191	4.699	
Q	.048	.054	1.219	1.372	
S	3°	6°	3°	6°	
Т	3°	6°	3°	6°	
U	3°	6°	3°	6°	
V	.094	.110	2.388	2.794	
W	.014	.025	.356	.635	
Х	3°	5.5°	3°	5.5°	
Y	.385	.410	9.779	10.414	
z	.130	.150	3.302	3.810	

## NOTE:

1. Dimension L, M, W apply for Solder Dip Finish



## **Recommended Solder Pad Layout**



TO-220-2

Part Number	Package	Marking
C2D05120A	TO-220-2	C2D05120

"The levels of environmentally sensitive, persistent biologically toxic (PBT), persistent organic pollutants (POP), or otherwise restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2002/95/EC on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April 21, 2006."

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.

Copyright © 2006-2009 Cree, Inc. All rights reserved. The information in this document is subject to change without notice. Cree, the Cree logo, and Zero Recovery are registered trademarks of Cree, Inc.

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Cree, Inc.: